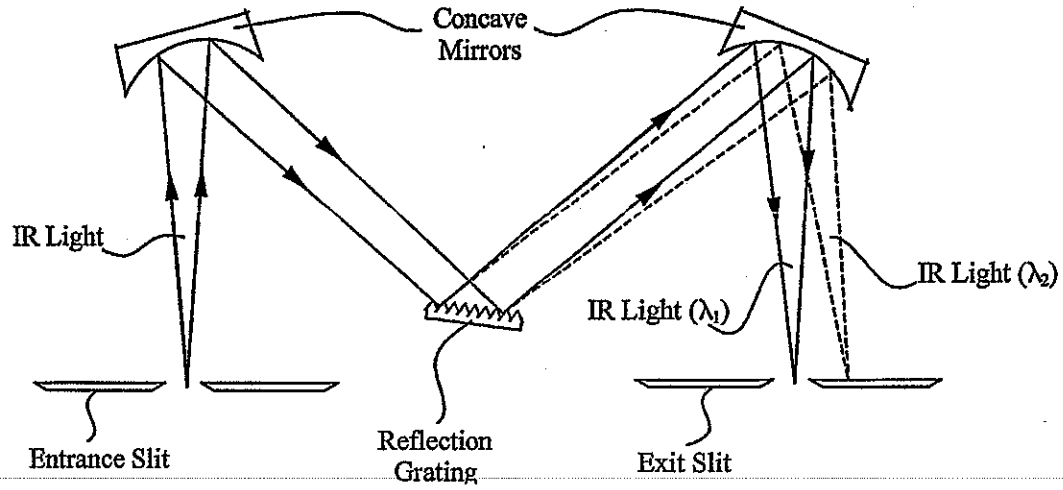


Figure 1A (PRIOR ART)

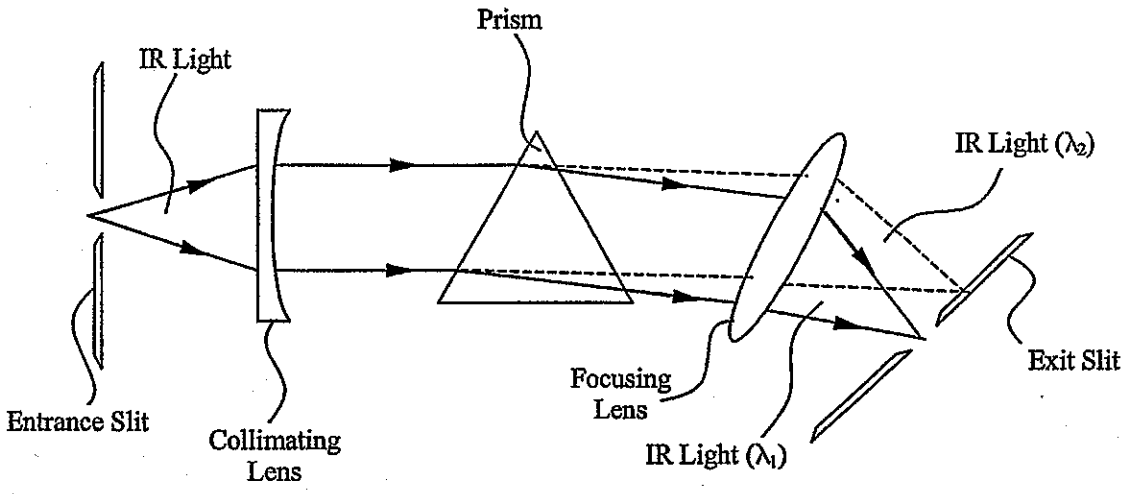


Figure 1B (PRIOR ART)

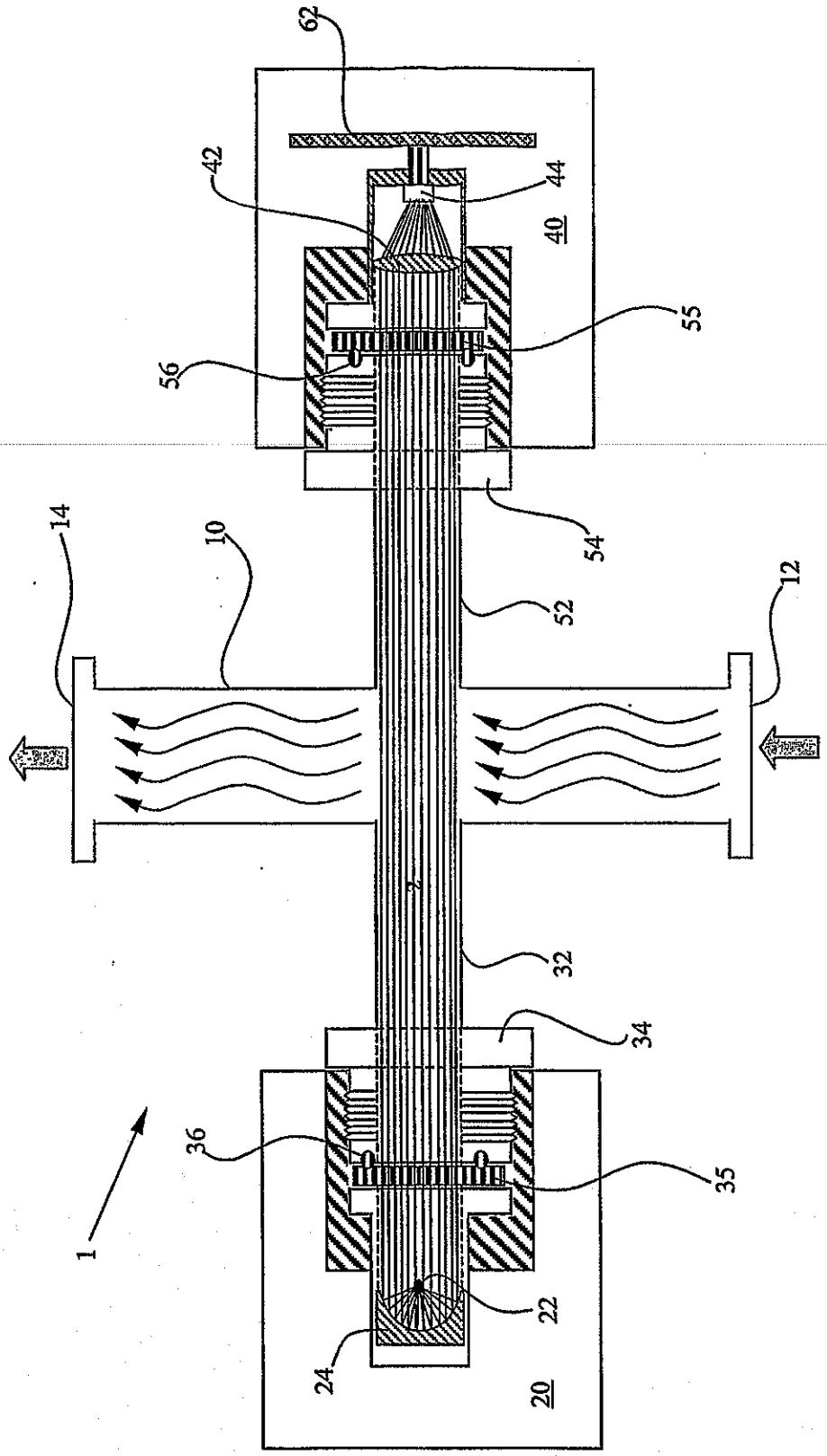


Figure 2

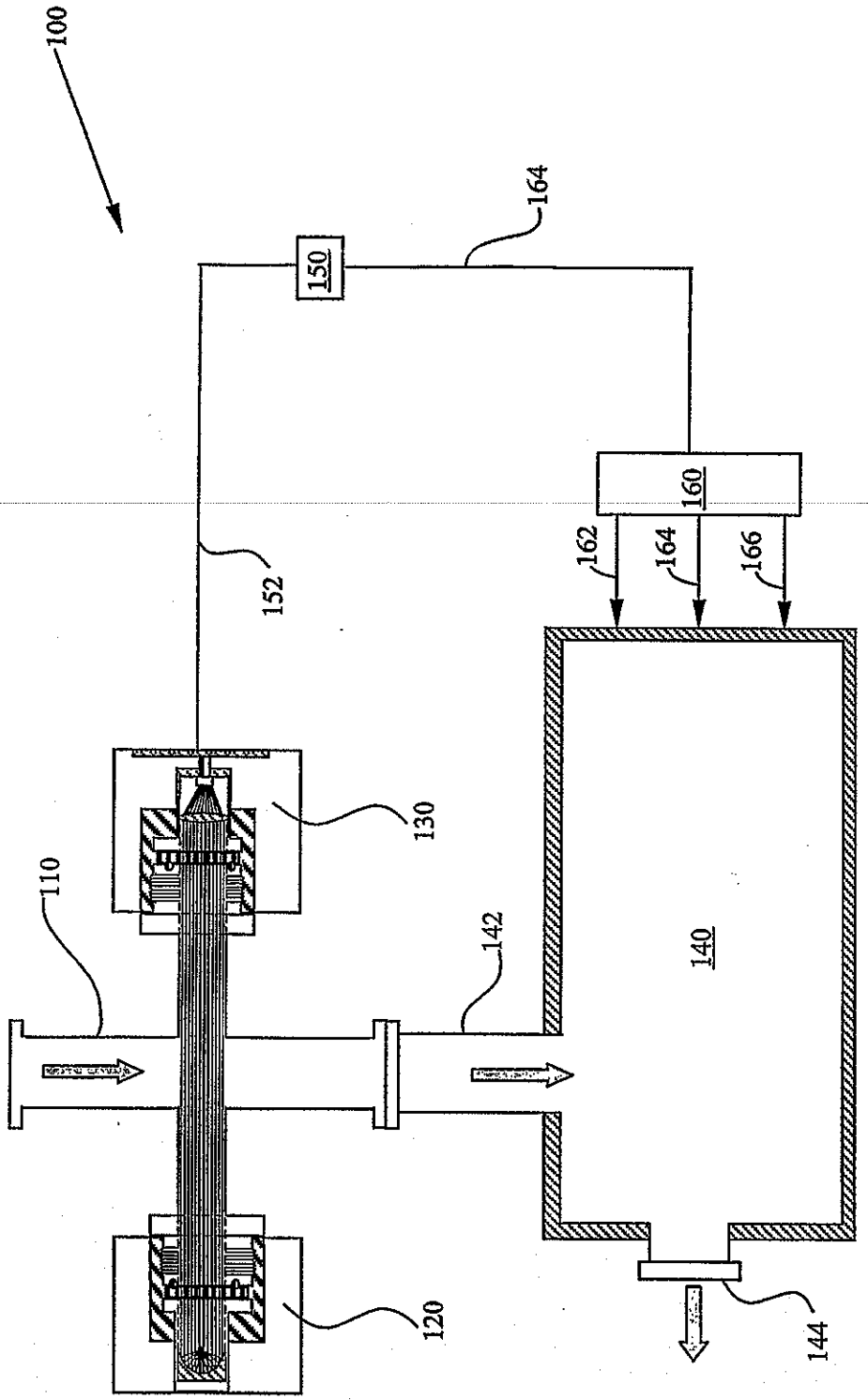


Figure 3

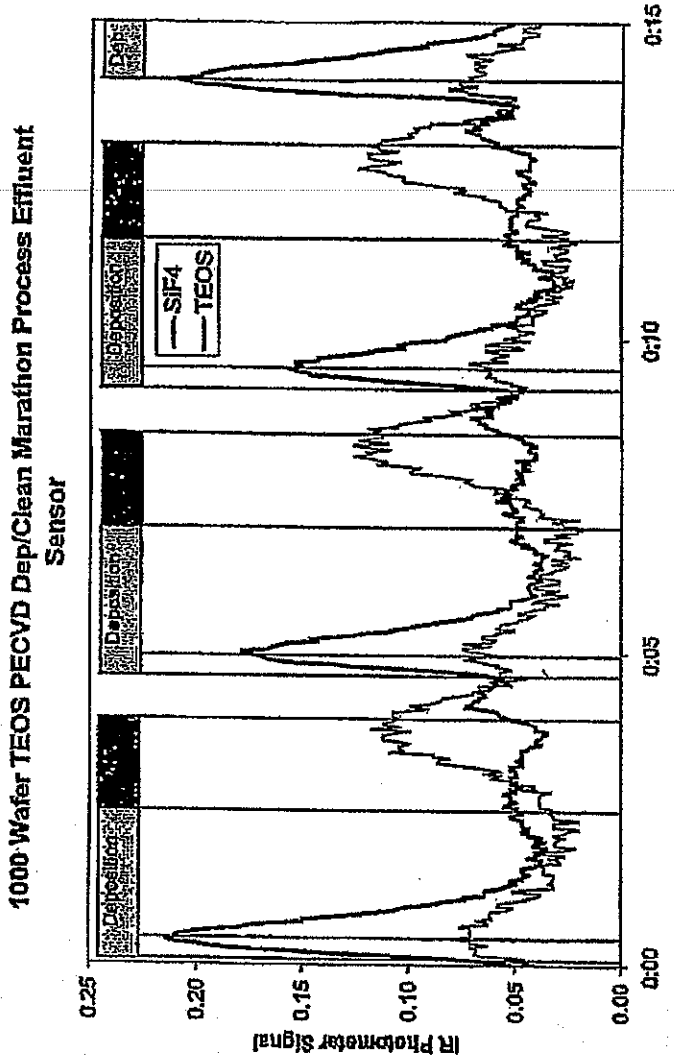

1000 Wafer TEOS PECVD Dep/Clean Marathon Process Effluent Sensor
IR Photometer Signal
0.25
0.20
0.15
0.10
0.05
0.00
0:00
0:05
0:10
0:15
Time (h:m)
SiF4
TEOS
Dep
Dep
Dep
Dep

Figure 4

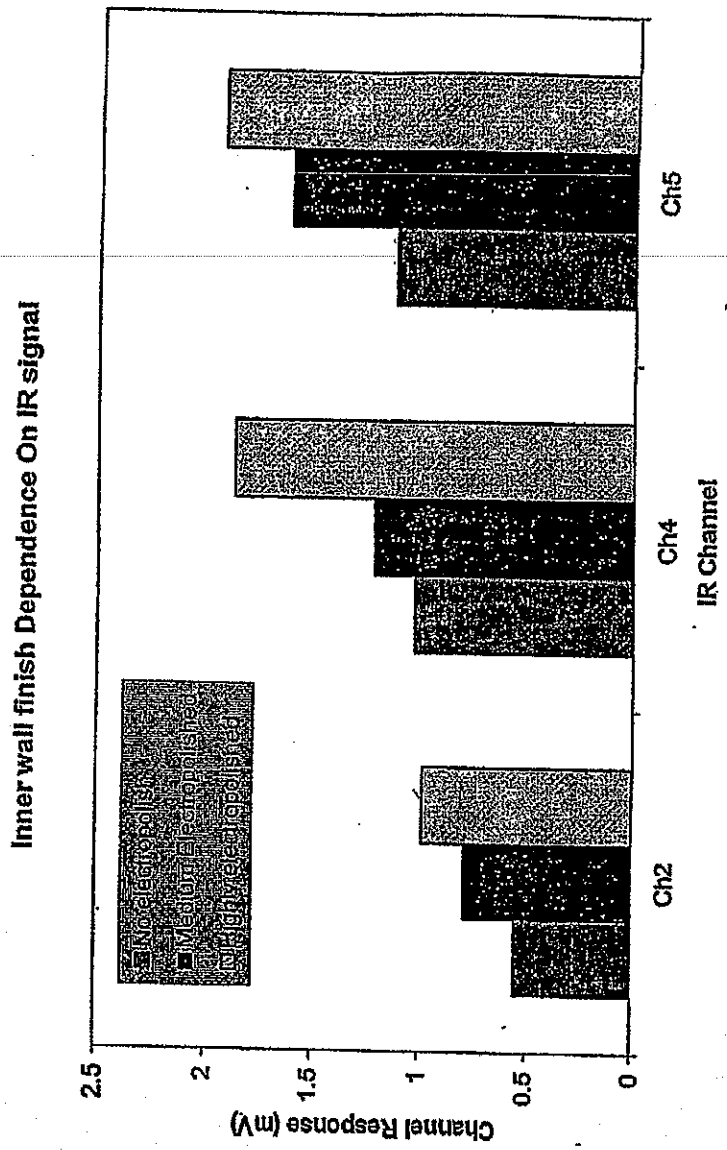

Inner wall finish Dependence On IR signal
Channel Response (mV)
2.5
2
1.5
1
0.5
0
Ch2
Ch4
Ch5
IR Channel

Figure 5

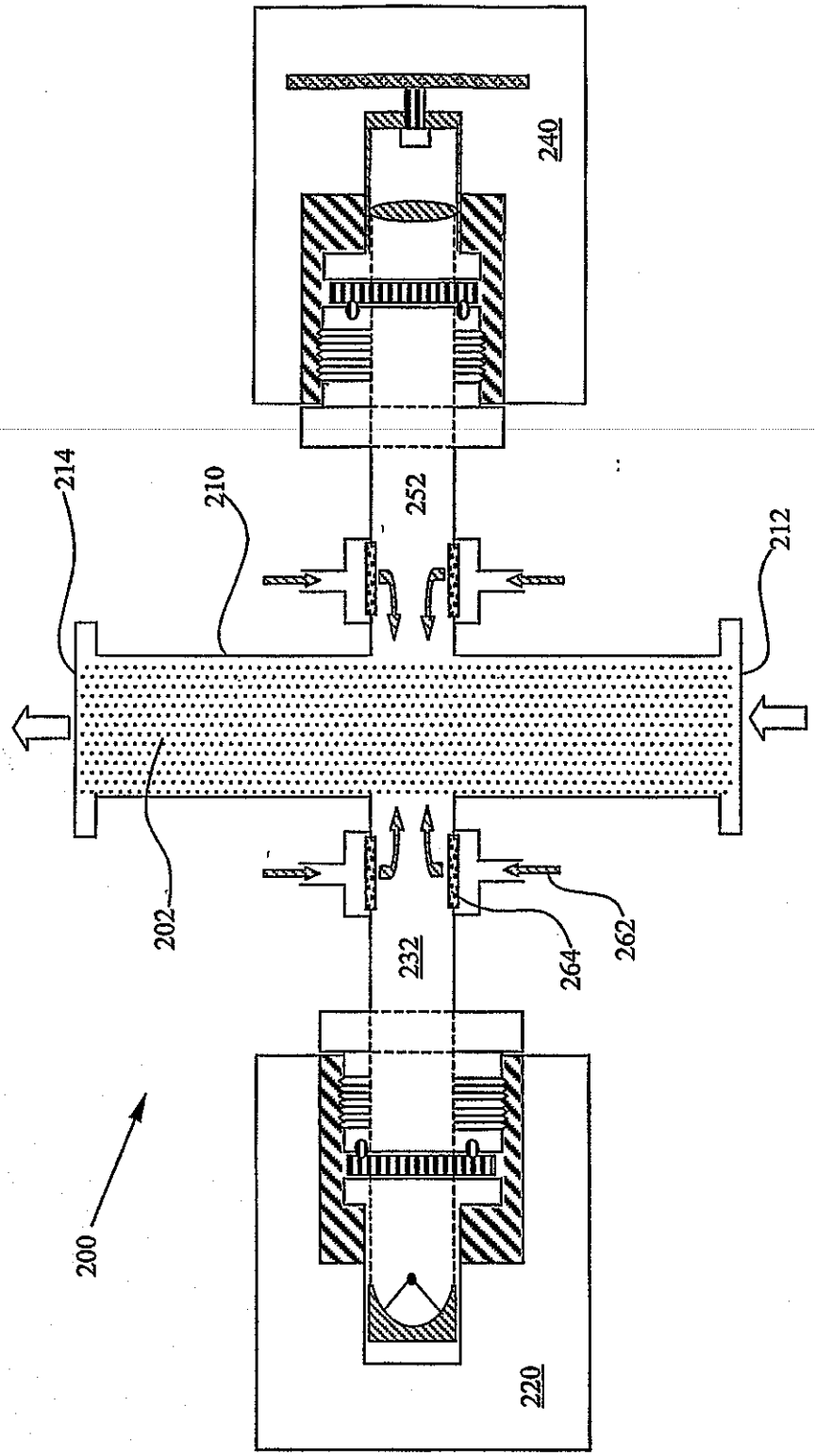


Figure 6

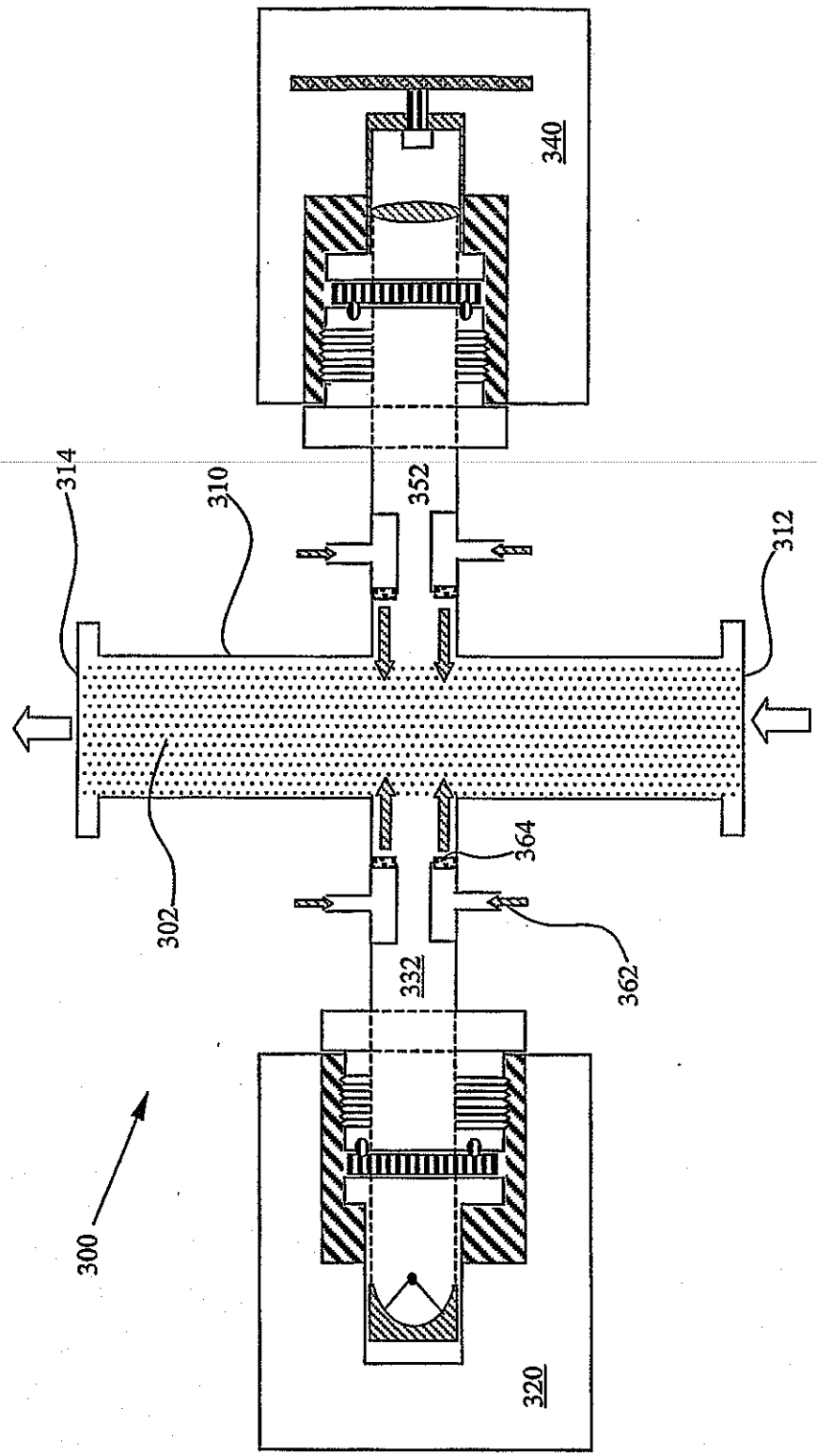


Figure 7